Title (en)

Read only storage matrix.

Title (de)

Festwertspeichermatrix.

Title (fr)

Matrice de mémoire morte.

Publication

EP 0041603 A1 19811216 (EN)

Application

EP 81102886 A 19810415

Priority

US 15792180 A 19800609

Abstract (en)

[origin: US4347585A] This matrix has high barrier Schottky diodes at Read or Reproduce Only Storage (ROS) matrix crossovers to represent 1's (the absence of diodes representing 0's) and low barrier Schottky diodes connected to select individual column lines (bit lines) of the ROS matrix. A current sink is connected to each column. Any unselected column causes the current in that column to be diverted through the respective low barrier diode, thus preventing that current from flowing into the selected word line. The only current that flows into the selected word line of a matrix depends from the single selected column current source.

IPC 1-7

G11C 17/06

IPC 8 full level

G11C 17/06 (2006.01); **G11C 17/08** (2006.01)

CPC (source: EP US)

G11C 17/06 (2013.01 - EP US); **G11C 17/08** (2013.01 - EP US)

Citation (search report)

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Designated contracting state (EPC)

DE FR GB

DOCDB simple family (publication)

EP 0041603 A1 19811216; **EP 0041603 B1 19840711**; DE 3164678 D1 19840816; JP S578993 A 19820118; JP S5855599 B2 19831210; US 4347585 A 19820831

DOCDB simple family (application)

EP 81102886 A 19810415; DE 3164678 T 19810415; JP 5067381 A 19810406; US 15792180 A 19800609